

GLOSSARY

In this document, unless the context otherwise requires, explanations and definitions of certain terms used in this document in connection with our Company and our business shall have the meanings set out below. The terms and their meanings may not always correspond to standard industry meaning or usage of these terms.

“ADAS”	advanced driver assistance system, referring to electronic systems developed to automate, adapt and enhance vehicle systems for safety and better driving
“ADC”	analog-to-digital converter, a device used to convert continuous analog signals into discrete digital signals
“AEC-Q”	standards established by the Automotive Electronics Council
“BCD”	bipolar-CMOS-DMOS, a key process technology for semiconductors. It is a family of silicon processes, each of which combines the strengths of three different process technologies onto a single chip: bipolar for precise analog functions, CMOS for digital design and DMOS (Double Diffused Metal Oxide Semiconductor) for power and high-voltage elements
“BMS”	battery management system
“CAGR”	compound annual growth rate
“CMOS”	complementary metal-oxide semiconductor
“CPU”	central processing unit, the general-purpose processor that fetches, decodes and executes program instructions, orchestrating virtually all computational tasks in a computer system
“DC”	direct current
“DFN”	dual-flat no-leads, a type of traditional packaging for power semiconductors
“EMI”	electromagnetic interference, a disturbance generated by external sources that affect an electrical circuit
“EV”	Electric vehicles
“FOM”	figure of merit, a quantitative measure used to evaluate and compare the performance of a device, system or method. It is a metric that helps assess performance relative to its alternatives

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“FRD Power Chip”	a type of fast recovering diode device that is used as a rectifier to convert alternating current to direct current
“GaN”	gallium nitride, a type of third-generation wide-bandgap semiconductor material. GaN’s advantages include wide bandgap, high saturation drift velocity and high critical breakdown electric field, making it ideal for high-power, high-temperature and high-frequency applications
“GPU”	graphics processing unit, a specialized electronic circuit designed to rapidly manipulate and alter memory to accelerate the creation of images
“IC” or “integrated circuit”	integrated circuit, a small unit or package which is made as a single indivisible structure (such as a chip) and is electrically equivalent to a conventional circuit of many separate components
“IDM”	integrated device manufacturer, a company that takes charge of design, manufacturing, packaging, testing and subsequent sales of the finished products
“IGBT”	insulated gate bipolar transistor(s), a type of transistor that combines the high efficiency and fast switching of a MOSFET with the high current and low saturation voltage of a bipolar transistor
“IoT”	internet of things, a network of interconnected devices that communicate and exchange data with each other over the internet
“ISO”	International Organization for Standardization
“ISO 14001”	Environmental Management Systems — Requirements with Guidance for Use, a standard for environmental management systems published by the ISO
“ISO 45001”	Occupational Health and Safety Management System — Requirements with Guidance for Use, an international standard for occupational health and safety management systems
“ISO 9001”	Quality Management Systems — Requirements, an international standard on quality management systems developed by the ISO
“LDO”	low dropout regulators, referring to devices that provide a stable voltage to various electronic systems within a vehicle and are used to convert the fluctuating voltage from the car battery into a steady, lower voltage required by sensitive electronic components

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“MEMS”	Micro-Electro-Mechanical Systems, miniature devices that integrate mechanical and electrical components
“MOS” or “MOSFET”	metal-oxide-semiconductor field-effect transistor, a type of transistor used to amplify or switch electronic signals
“OEM”	Original equipment manufacturing, whereby products are manufactured in accordance with a customer’s specifications for sale by customers under the customer’s or third-party’s brand
“on-resistance”	the resistance value between the drain and source of a MOSFET when it is turned on. It is measured by evaluating the voltage drop from drain to source under specific conditions. The smaller this value is, the lower the power loss
“PCB”	printed circuit board, a board with electronic circuits connecting various components
“Planar MOSFET”	a type of MOSFET, featuring a simple structure with a gate electrode placed on the surface of the wafer, separated by a thin oxide layer
“RoHS”	Restriction of Hazardous Substances Directive of the European Union, which restricts the use of certain hazardous materials found in electrical and electronic equipment
“R _{sp} ”	specific on-resistance, a key parameter indicating the resistance of a MOSFET when it is turned on, normalized by the active area. R _{sp} impacts conduction losses and overall efficiency. Smaller R _{sp} value indicates better the performance of the power semiconductor device
“R&D”	research and development
“SGT MOSFET”	shielded gate trench MOSFET, a type of MOSFET where deep trenches are etched into the silicon wafer, embedding the gate electrode within the trench
“SiC”	silicon carbide, a semiconductor material used in various electronic applications
“SJ MOSFET”	super junction MOSFET, a type of MOSFET based on super junction technology
“SOP”	small outline packaging, a type of traditional packaging for power semiconductors

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“Tier-1 suppliers”	automotive system integrator(s), company(ies) that supply(ies) assembled components or systems directly to OEMs. Tier-1 suppliers need to work closely with OEMs during the design and development stages of vehicles, ensuring the integration of their components into the final product
“Trench MOSFET”	a type of MOSFET, featuring a vertical structure where the gate electrode is embedded in a trench, which enables high cell density to achieve low conduction loss.
“VCE (sat)”	the collector-emitter saturation voltage in a bipolar junction transistor
“VDMOS”	vertical double diffused metal oxide semiconductor, a type of power MOSFET particularly suited for high-current, high-voltage applications characterized by a vertical current flow
“Vth”	the minimum gate-to-source voltage that is needed to create a conducting path between the source and drain of a MOSFET
“wafer”	a thin slice of semiconductor material, such as a silicon crystal, on which arrays of integrated circuits or discrete devices are fabricated during the manufacturing process
“WLCSP”	Wafer Level Chip Scale Package, the technology of packaging an integrated circuit at the wafer level, instead of the traditional process of assembling individual units in packages after dicing them from a wafer